



VDRM

T(AV)

Iтѕм dV/dt\*

dl/dt

**KEY PARAMETERS** 

5200V

3990A

53300A

2000V/µs

1000A/µs

\* Higher dV/dt selections are available on request



#### Replaces DS5940-5

Phase Control Thyristor

| DS5940-6 March 2022 (LN41635 | DS5940-6 | March 2022 | (LN41635) |
|------------------------------|----------|------------|-----------|
|------------------------------|----------|------------|-----------|

### **FEATURES**

- Double Side Cooling
- High Surge Capability

#### **APPLICATIONS**

- Crowbar
- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

| Part and<br>Ordering<br>Number          | Repetitive<br>Peak Voltages<br>VDRM and VRRM<br>(V) | Conditions   |
|---|---|--|
| DCR3990A52*<br>DCR3990A50<br>DCR3990A45 | 5200<br>5000<br>4500                                | $T_{vj} = -40^{\circ}C$ to 125°C,<br>IDRM = IRRM = 300mA,<br>VDRM, VRRM t <sub>P</sub> = 10ms<br>VDSM & VRSM =<br>VDRM & VRRM + 100V<br>respectively |

Lower voltage grades available.

\*5000V @ -40°C, 5200V @ 0°C

### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR3990A52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

# Outline type code: A (See Package Details for further information)

Fig. 1 Package outline

# **CURRENT RATINGS**

T<sub>case</sub> = 60°C unless stated otherwise

| Symbol    | Parameter                            | Test Conditions          | Max. | Units |
|-----------|--------------------------------------|--------------------------|------|-------|
| Double Si | de Cooled                            |                          |      |       |
| Ιτ(Αν)    | Mean on-state current                | Half wave resistive load | 3990 | А     |
| It(rms)   | RMS value                            | -                        | 6270 | А     |
| Іт        | Continuous (direct) on-state current | -                        | 5640 | А     |

## SURGE RATINGS

| Symbol | Parameter                               | Parameter Test Conditions     |      | Units             |
|--------|---|-------------------------------|------|-------------------|
| Ітѕм   | Surge (non-repetitive) on-state current | 10ms half sine, Tcase = 125°C | 53.3 | kA                |
| l²t    | I <sup>2</sup> t for fusing             | VR = 0                        | 14.2 | MA <sup>2</sup> s |

# THERMAL AND MECHANICAL RATINGS

| Symbol   | Parameter                                      | Test Conditions          |             |     | Max. | Units |
|----------|--|--------------------------|-------------|-----|------|-------|
|          |  | Double side cooled       | DC          | -   | 6.0  | °C/kW |
| Rth(j-c) | Rth(j-c) Thermal resistance - junction to case |                          | Anode DC    | -   | 10.4 | °C/kW |
|          |  | Single side cooled       | Cathode DC  | -   | 14.9 | °C/kW |
| Back     | Rth(c-h) Thermal resistance - case to heatsink | Clamping force 83kN      | Double side | -   | 1.0  | °C/kW |
| rtn(c-n) |  | (with mounting compound) | Single side | -   | 2.0  | °C/kW |
| Tvj      | Virtual junction temperature                   | Blocking Vdrm / Vrrm     |             | -   | 125  | °C    |
| Tstg     | Storage temperature range                      |                          |             | -55 | 125  | °C    |
| Fm       | Clamping force                                 |                          |             | 74  | 91   | kN    |

# **DYNAMIC CHARACTERISTICS**

| Symbol         | Parameter                                     | Test Conditior  | IS                 | Тур. | Max. | Units |
|----------------|---|---|--------------------|------|------|-------|
| 1              | Deals reverse and aff state average           | At VRRM/VDRM, Tcase = 125°C   |                    | -    | 300  | mA    |
| Irrm/Idrm      | Peak reverse and off-state current            | At 50% VRRM/VDRM, Tcase = 7   | 125°C              | 20   | -    | mA    |
| Symbol         | Parameter                                     | Test Condition  | IS                 | Min. | Max. | Units |
| Vтм            | Instantaneous forward voltage                 | At 4000A peak, Tj = 125°C   |                    | 1.45 | 1.65 | V     |
| dV/dt          | Max. linear rate of rise of off-state voltage | То 67% Vdrm, Tj = 125°С, g  | ate open           | -    | 2000 | V/µs  |
| dl/dt          | Rate of rise of on-state current              | From 67% VDRM to 2x IT(AV)<br>Gate source 30V, $10\Omega$                                   | Repetitive<br>50Hz | -    | 400  | A/µs  |
| avat           |   | tr < 0.5µs, Tj = 125°C  | Non-repetitive     | -    | 1000 | A/µs  |
| Veren          | Threshold voltage - Low level                 | 500A to 3600A at T <sub>case</sub> = 125°C  |                    | -    | 0.85 | V     |
| <b>V</b> τ(το) | Threshold voltage - High level                | 3600A to 9000A at Tcase = 125°C   |                    | -    | 1.03 | V     |
| -              | On-state slope resistance - Low level         | 500A to 3600A at Tcase = 125°C  |                    | -    | 0.21 | mΩ    |
| ľτ             | On-state slope resistance - High level        | 3600A to 9000A at Tcase = 125°C   |                    | -    | 0.16 | mΩ    |
| tgd            | Delay time                                    | $V_D = 67\% V_{DRM}$ , gate source 30V, 10 $\Omega$<br>tr = 0.5µs, Tj = 25°C                |                    | -    | 3    | μs    |
| tq             | Turn-off time                                 | $T_j = 125^{\circ}C$ , $V_R = 200V$ , $dI/dt = 1A/\mu s$<br>$dV_{DR}/dt = 20V/\mu s$ linear |                    | -    | 750  | μs    |
| Qs             | Stored charge                                 | I⊤ = 1500A, Tj = 125°C, dl/dt = 1A/µs,  |                    | 3870 | 8340 | μC    |
| Irr            | Reverse recovery current                      | V <sub>R</sub> ~ 2100V, Cs = 1μF, Rs = 63Ω  |                    | 51   | 83   | А     |
| IL.            | Latching current                              | Tj = 25°C, VD = 5V  |                    | -    | 3    | А     |
| Ін             | Holding current                               | Тј = 25°С, Rg-к = ∞, Iтм = 50   | 0A, I⊤ = 5A        | -    | 300  | mA    |

# GATE TRIGGER CHARACTERISTICS AND RATINGS

| Symbol | Parameter                | Test Conditions            | Max. | Units |
|--------|--------------------------|----------------------------|------|-------|
| Vgт    | Gate trigger voltage     | Vdrm = 5V, Tcase = 25°C    | 1.5  | V     |
| Vgd    | Gate non-trigger voltage | At 50% Vdrm, Tcase = 125°C | 0.4  | V     |
| Іст    | Gate trigger current     | Vdrм = 5V, Tcase = 25°С    | 400  | mA    |
| Igd    | Gate non-trigger current | At 50% Vdrм, Tcase = 125°С | 10   | mA    |

## CURVES

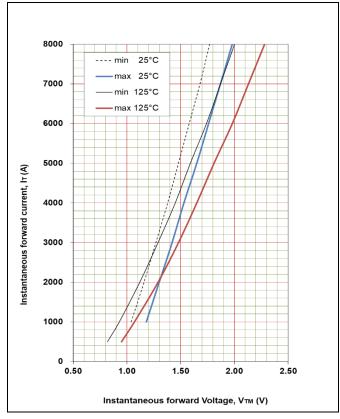


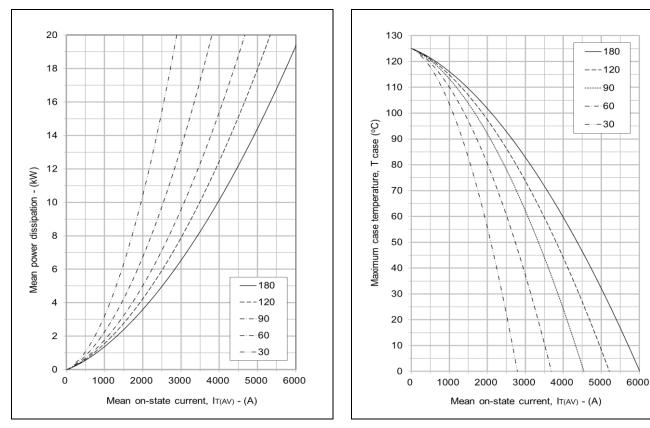
Fig. 2 Maximum & minimum on-state characteristics

# **VTM EQUATION**

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.061663 B = 0.116682 C = 0.000119 D = 0.002396 These values are valid for  $T_j = 125^{\circ}C$  for IT 500A to 9000A

# DCR3990A52



@2 ion

Fig. 3 On-state power dissipation - sine wave

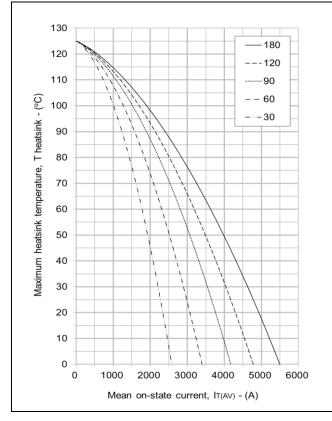


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

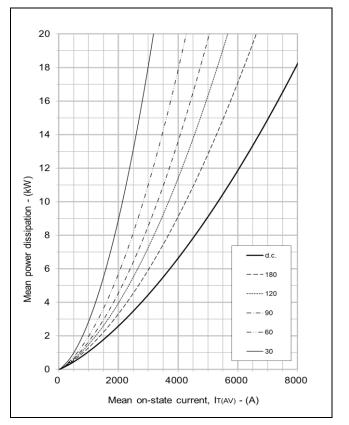


Fig. 6 On-state power dissipation - rectangular wave

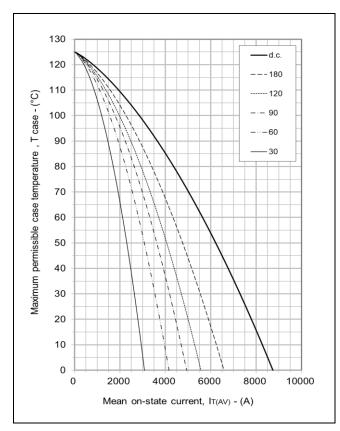
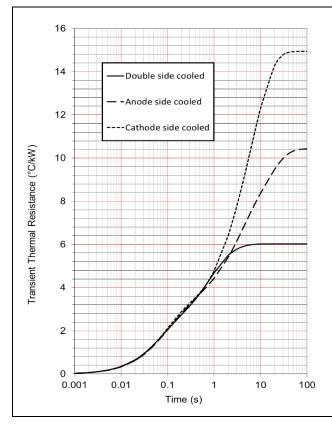


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



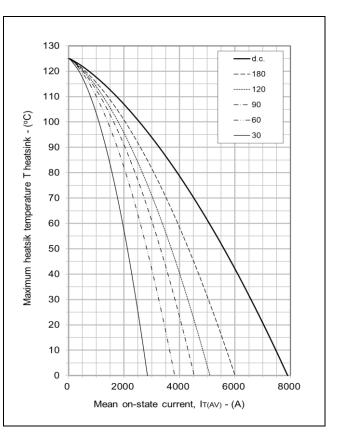


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

|              |           | 1     | 2      | 3     | 4     |
|--------------|-----------|-------|--------|-------|-------|
| Double side  | Ri(°C/kW) | 3.015 | 1.049  | 0.984 | 0.984 |
| cooled       | Ti(s)     | 0.704 | 1.905  | 0.059 | 0.059 |
| Anode side   | Ri(°C/kW) | 3.156 | 4.093  | 1.557 | 1.624 |
| cooled       | Ti(s)     | 2.690 | 13.792 | 0.059 | 0.206 |
| Cathode side | Ri(°C/kW) | 7.077 | 3.483  | 1.746 | 2.634 |
| cooled       | Ti(s)     | 6.649 | 8.436  | 1.762 | 0.081 |

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{th(j-c)}$  Conduction

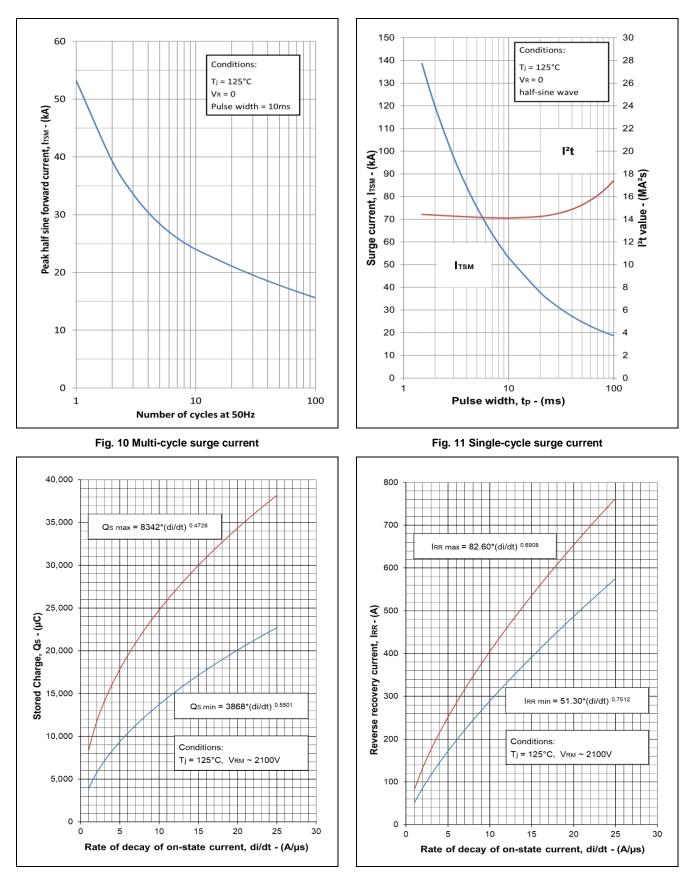
Tables show the increments of thermal resistance R  $_{\text{frij-ej}}$  when the device operates at conduction angles other than d.c.

| D   | ouble side cooling Anode Side Cooling |       |     | Cath               | ode Side | d Cooling          |     |       |       |    |                   |
|-----|---------------------------------------|-------|-----|--------------------|----------|--------------------|-----|-------|-------|----|-------------------|
|     | $\Delta Z_{th}$                       | (z)   |     | $\Delta Z_{th}(z)$ |          | $\Delta Z_{th}(z)$ |     |       |       | ΔZ | <sub>th</sub> (z) |
| θ°  | sine.                                 | rect. | θ°  | sine.              | rect.    | I I                | θ°  | sine. | rect. |    |                   |
| 180 | 0.44                                  | 0.31  | 180 | 0.42               | 0.30     | Ιſ                 | 180 | 0.42  | 0.30  |    |                   |
| 120 | 0.49                                  | 0.43  | 120 | 0.47               | 0.41     | 1 [                | 120 | 0.47  | 0.41  |    |                   |
| 90  | 0.55                                  | 0.49  | 90  | 0.52               | 0.46     | Ιſ                 | 90  | 0.52  | 0.46  |    |                   |
| 60  | 0.60                                  | 0.55  | 60  | 0.57               | 0.52     | Í                  | 60  | 0.57  | 0.52  |    |                   |
| 30  | 0.64                                  | 0.61  | 30  | 0.61               | 0.58     |                    | 30  | 0.60  | 0.58  |    |                   |
| 15  | 0.66                                  | 0.64  | 15  | 0.62               | 0.61     | ΙC                 | 15  | 0.62  | 0.60  |    |                   |

Fig.9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

@2 ion

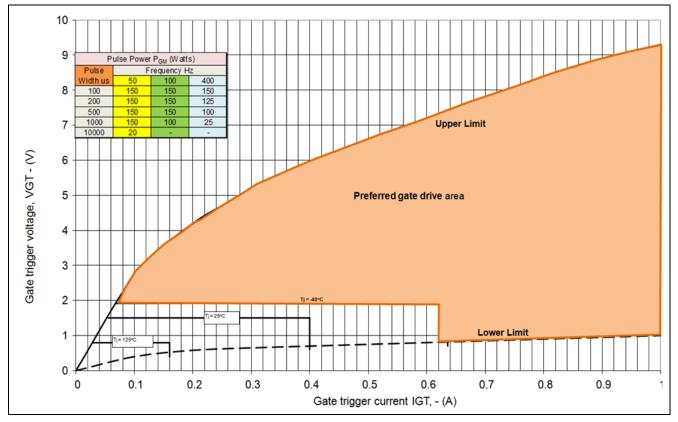
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Fig. 12 Stored charge

Fig. 13 Reverse recovery current



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Fig.14 Gate characteristics

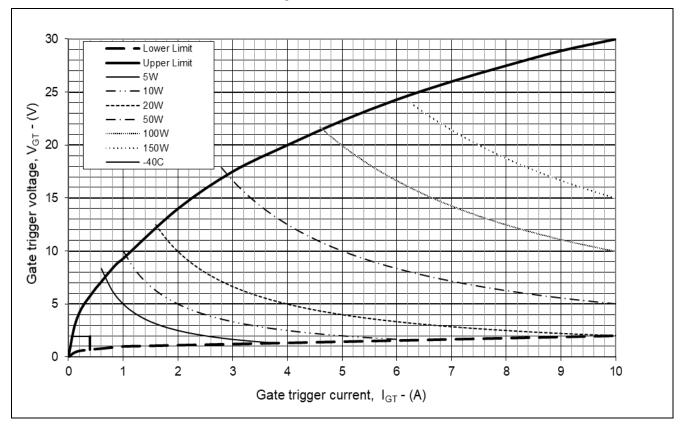


Fig. 15 Gate characteristics

## **PACKAGE DETAILS**

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

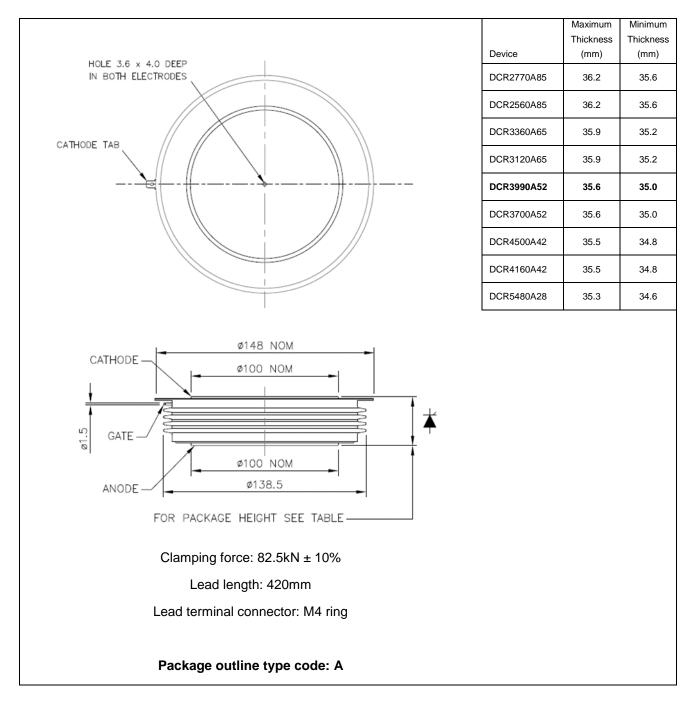


Fig. 16 Package outline

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